Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	forming adj sidewall same crystal structure and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:04
L2	1	forming adj sidewall same restore with crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:05
L3	0	forming adj sidewall same heat treatment same restore with crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:05
L4	35	forming adj sidewall same heat treatment and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:16
L5	3	forming adj sidewall same heat treatment same annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:08
L6	0	forming adj sidewall same heat treatment same recrystallize and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:09
L7	1	forming adj sidewall same heat treatment same crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:09
L8	15	forming adj sidewall with heat treatment and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:16
L9	1	forming adj sidewall with during with heat treatment and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:16
L10	1319376	heat treatment same form same sidewalls same crystal	US-PGPUB; USPAT	OR	ON	2007/06/04 08:26
L11	39	heat treatment same form same sidewalls same crystal	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:26
L12	0	heat treatment near form near sidewalls same crystal	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:26
L13	1	heat treatment with form near sidewalls same crystal	US-PGPUB; USPAT	ADJ	ON	2007/06/04 08:26
L24	13	"6074937"	US-PGPUB; USPAT	OR	ON	2007/06/04 11:02
L25	15	"6180476"	US-PGPUB; USPAT	OR	ON	2007/06/04 11:03
L26	. 5	"6699771"	US-PGPUB; USPAT	OR	ON	2007/06/04 11:04
L27	2	"6391751"	US-PGPUB; USPAT	OR	ON	2007/06/04 11:04
L28	8	"6472282"	US-PGPUB; USPAT	OR	ON	2007/06/04 11:05
L29	1	"20020068407"	US-PGPUB; USPAT	OR	ON	2007/06/04 11:05

L30	15	"6521502"	US-PGPUB; USPAT	OR	ON	2007/06/04 11:05
S1	.1	("6074937").PN.	US-PGPUB; USPAT	OR	OFF	2007/05/23 09:16
S2	3	("5254484"   "5585286"   "5953615").PN.	US-PGPUB; USPAT; USOCR	OR .	ON	2007/05/23 09:38
S3	2	("4584026"   "5266510").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/23 09:24
S4	45	shibata-satoshi.in.	US-PGPUB; USPAT	OR	ON	2007/05/30 09:02
S5 .	1	"04058524"	US-PGPUB; USPAT	OR	ON	2007/05/23 09:45
S6	2	"04058524"	US-PGPUB; USPAT; JPO	OR	ON	2007/05/29 10:13
S7	3	"04058524" ,	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/29 15:03
S33	3518	438/197	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/23 11:14
S34	1352	438/197 and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/23 11:17
S35	84	pn adj junction and 438/197 and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/23 11:18

S36	2	amorphous same pn adj junction and 438/197 and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/23 12:32
S37	21	"5602045"	US-PGPUB; USPAT	OR	ON	2007/05/23 12:33
S38	14	"6521502"	US-PGPUB; USPAT; JPO	OR	ON	2007/05/24 08:34
S39	5	"6699771"	US-PGPUB; USPAT; JPO	OR	ON	2007/05/24 08:35
S40	6	("20020187614"   "5407838"   "5885886"   "5994175"   "6069062"   "6521502").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 08:38
S41	5	("3925106"   "4187125"   "4584026"   "5015593"   "5126278").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/24 09:51
S42	21	"5602045"	US-PGPUB; USPAT	OR	ON	2007/05/24 10:39
S43	9	"6319798"	US-PGPUB; USPAT	OR	ON	2007/05/24 15:21
S44	61	"6015739"	US-PGPUB; USPAT	OR	ON	2007/05/24 15:22
S45	0	dense same dispersed adj gate	US-PGPUB; USPAT	OR	ON	2007/05/24 15:22
S46	0	dense same dispersed near gate adj electrode	US-PGPUB; USPAT	OR	ON	2007/05/24 15:23
S47	0	dense same disperse near gate adj electrode	US-PGPUB; USPAT	OR .	ON	2007/05/24 15:23
S48	8	non-uniform near gate adj electrode	US-PGPUB; USPAT	OR	ON	2007/05/24 16:29
S49	6	"2007002"	US-PGPUB; USPAT	OR	ON	2007/05/24 16:30
S50	1	"20070042542"	US-PGPUB; USPAT	OR	ON	2007/05/24 16:30
S51	342	yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 14:34
S52	158	drain adj extensions and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 11:38
S53	3	drain adj extensions same "15" adj nm and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/25 10:52

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S54	184	forming adj sidewall same annealing	US-PGPUB; USPAT	OR	ON	2007/05/29 10:14
S55	90	forming adj sidewall same annealing and @py<"2004"	US-PGPUB; USPAT	OR	ON	2007/05/29 10:53
S56	7686914	forming adj sidewall same annealing same haloand @py<"2004"	US-PGPUB; USPAT	OR	ON	2007/05/29 10:54
S57	1	forming adj sidewall same annealing same halo and @py<"2004"	US-PGPUB; USPAT	OR	ON	2007/05/29 10:54
S58	13	("6153455"   "6238960"   "6251761"   "6287924"   "6361874"   "6365476"   "6368947"   "6380044"   "6420264"   "6472277"   "6551888"   "6555439"   "6559015").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/29 10:58
S59	227	sidewall same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/29 10:59
S60	109	sidewall same crystal structure and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:00
S61	691	sidewall with annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:00
S62	. 11	sidewall near gate electrode with annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:28
S63	21	annealing same during with formation with sidewall and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:14
S64	6	annealing same during near formation with sidewall and @py<"2004"	US-PGPUB; USPAT	ADJ	ON.	2007/05/29 11:35
S65	1	annealing same during near formation near sidewall and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:35
S66	0	annealing near during near formation near sidewall and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:36
S67	97	during near formation near sidewall and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:36
S68	0	during near formation near sidewall same annealling and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:36
S69	1	during near formation near sidewall same annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:36
S70	0	during near formation near sidewall near annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:36
S71	0	formation near sidewall near annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:37

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S72	42	sidewall near annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 11:37
S73	342	drain adj extensions same sidewallsand yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 11:38
S74	90	drain adj extensions same sidewalls and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 11:40
S75	0	annealing same during near formation near sidewalls and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 11:40
S76	1	during near formation near sidewalls and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 11:41
S77	0	annealing same during with formation near sidewalls and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 11:41
S78	0	annealing same during same formation near sidewalls and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 12:08
S79	0	annealing same during formation near sidewalls and yu-bin.in.	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:08
S80	1	annealing same during formation near sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:08
S81	0	annealing during formation near sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:08
S82	0	annealing during formation sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:09
S83	. 0	crystallization during formation sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:09
S84	0	crystal structure near during formation sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:09
S85	0	crystal structure near during sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:10
S86	. 64	crystal near sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:10
S87	11	anneal near sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:10
S88	0	formation near sideawalls same during annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:16
S89	5	formation near sidewalls same during annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:17
S90	0	formation near sapacers same during annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:17
S91	2	formation near spacers same during annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:17

S92	0	during near formation near spacers	US-PGPUB;	ADJ	ON	2007/05/29 12:17
		same during annealing and @py<"2004"	USPAT			
S93	2	during same formation near spacers same during annealing and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:18
S94	3	annealing same simultaneously same formation near sidewalls and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:19
S95	1	annealing same simultaneously same formation near spacers and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 12:19
S96	1	CVD same "550" and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 14:35
S97	0	CVD same (sidewalls or spacers) same "550" and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 14:35
S98	42	CVD same (sidewalls or spacers) and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 14:37
S99	1	CVD same (sidewalls or spacers)same anneal and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 14:38
S10 0	39	(sidewalls or spacers)same anneal and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 14:39
S10 1	442	CVD same(sidewalls or spacers)same heat treatment same crystal and yu-bin.in.	US-PGPUB; USPAT	OR	ON	2007/05/29 14:39
S10 2	0	CVD same(sidewalls or spacers)same heat treatment same crystal and yu-bin.in.	US-PGPUB; USPAT	ADJ	ON	2007/05/29 14:39
S10 3	19	CVD same(sidewalls or spacers)same heat treatment same crystal	US-PGPUB; USPAT	ADJ	ON	2007/05/29 14:41
S10 4	293	CVD same(sidewalls or spacers) same anneal	US-PGPUB; USPAT	ADJ	ON	2007/05/29 14:42
S10 5	171	CVD same(sidewalls or spacers) same anneal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 14:43
S10 6	15	CVD same(sidewalls or spacers) same amorphous same crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 14:47
S10 7	218	CVD same(sidewalls or spacers) same crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 14:48
S10 8	14	(sidewalls or spacers) formed same CVD same crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 14:48

S10 9	366712	sidewalls or spacers same formed same cvd same heat treatment same amorphous same crystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:04
S11 0	3	(sidewalls or spacers) same formed same cvd same heat treatment same amorphous same crystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:06
S11 1	0	(sidewalls or spacers) near cvd same heat treatment same amorphous same crystal	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:06
S11 2	1	(sidewalls or spacers) near cvd same amorphous	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:07
S11 3	0	PEVCD same spacers same "500"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:07
S11 4	249	PECVD same spacers same "500"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:09
S11 5	0	PECVD near spacers same "500"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:09

S11 6		PECVD near sidwalls same "500"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:09
S11 7	0	PECVD near sidwalls	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:10
S11 8	10	PECVD near sidewalls	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:12
S11 9	0	dielectric spacers formed by CVD	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:12
S12 0	0	dielectric spacers formed CVD	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:12
S12 1	234	dielectric spacers same CVD	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:12
S12 2	141	dielectric spacers same CVD and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:18

S12 3	2	dielectric spacers same CVD same amorphous and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 15:18
S12 4	3	("5543345"   "5700731"   "5792689").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/29 15:21
S12 5	27	CVD same 500C	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/29 15:22
S12 6	212	chemical vapor deposition same dielectric spacer	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/05/29 15:23
S12 7	154	chemical vapor deposition same dielectric spacer and @py<"2004"	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/05/29 15:25
S12 8	9	chemical vapor deposition same dielectric spacer same amorphous and @py<"2004"	US-PGPUB; USPAT; USOCR	ADJ	ON	2007/05/29 15:26
S12 9	38	("4683645"   "4697333"   "4745082"   "4784718"   "4954867"   "5264382"   "5374575"   "5391510"   "5393685"   "5429956"   "5478776"   "5593907"   "5607884"   "5654570"   "5675159"   "5716861"   "5753958"   "5770485"   "5793090"   "5811323"   "5825066"   "5856225"   "5888843"   "5885886"   "5915182"   "5915196"   "6004852"   "6008111"   "6022785"   "6037204"   "6114211"   "6133082"   "6165858"   "6194748"   "6204138"   "6268640"   "6361874"   "6365476").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/29 15:31
S13 0	18	CVD same change crystalline	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:32
S13 1	0	(sidewalls or spacers) same CVD same change crystalline	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:32
S13 2	0	CVD same (sidewalls or spacer)same change crystalline	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:33
S13 3	18	CVD same change crystalline	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:34
S13 4	0	(spacer or sidewall) formation same change crystalline	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:35

S13 5	14	(spacer or sidewall) same change crystalline	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:37
S13 6	0	(spacer or sidewall) same heat treatment same change crystalline	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:37
S13 7	36	heat treatment same change crystalline	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:56
S13 8	0	sidewalls same heat treatment same change crystalline	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:38
S13	0	spacers same heat treatment same change crystalline	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:38
S14 0	0	heat treatment same spacers same change crystalline	US-PGPUB; USPAT	ADJ	ON .	2007/05/29 15:38
S14 1	831	high temperature same forming same spacers	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:56
S14 2	572	high temperature same forming same spacers and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:56
S14 3	109	high temperature same forming near spacers and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:57
S14 4	1	high temperature same lpcvd same forming near spacers and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:58
S14 5	572	forming same spacers same high temperatures and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:58
S14 6	. 3	forming near spacers near high temperatures and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 15:59
S14 7	49	forming near spacers with high temperatures and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/29 16:05
S14 8	71	forming near spacers with high temperatures and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:08
S14 9	4	forming near spacers near high temperatures and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:08

S15 0	4	forming near spacers high temperatures and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:13
S15 1	0	high temperature chemical vapor deposition same spacers same change near crystalline	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:13
S15 2	12	high temperature chemical vapor deposition same spacers	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:16
S15 3		high temperature chemical vapor deposition same spacers same change crystalline	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:16
S15 4	1	forming adj spacer same high temperature CVD and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:40
S15 5	2	("5847427"   "6040216").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/29 16:39
S15 7	0	forming adj spacer same high temperature CVD same anneal and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:41

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S15 8	. 0	forming adj spacer same high temperature CVD same amorphous and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:41
S15 9	0	forming adj spacer same high temperature CVD same crystalline region and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:41
S16 0	0	forming adj spacer same high temperature process same crystalline and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:42
S16 1	1	forming adj spacer same high temperature same crystalline and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:42
S16 2	1	forming adj spacer same heat treatment same crystalline and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/29 16:47
S16 3	56	"6475869"	US-PGPUB; USPAT	OR	ON	2007/05/29 16:47
S16 4	0	sidewalls same high temperature cvd same restore crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:31
S16 5	0	sidewalls same high temperature cvd same crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:31
S16 6	7	sidewalls same high temperature cvd and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:33
S16 7.	0	sidewalls same high temperature cvd same amorphous and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:46
S16 8	0	forming sidewalls same while restor\$ same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:47

S16 9	0	sidewalls same while restor\$ same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:47
S17 0	6	sidewalls same restor\$ same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:49
S17	5	form same sidewalls same restor\$ same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:49
S17 2	0	form same sidewalls same cvd same restor\$ same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:49
S17 3	. 94	form same sidewalls same form same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:56
S17 4	0	form same crystal structure same high temperature cvd	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:52
S17 5	249	form same crystal structure same cvd	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:52
S17 6	4	form same crystal structure same cvd same sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:53
S17 7	0	form sidewalls same rapid thermaol oxidation same restore same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:53
S17 8	0	form sidewalls same rapid thermal oxidation same restore same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:53
S17 9	0	form sidewalls same thermal same restore same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:53
S18 0	0	form sidewalls same heat same restore same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:54
S18 1	0	sidewalls same heat same restore same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:54
S18 2	1	sidewalls same process same restore same crystal structure	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:54
S18 3	3	form same sidewalls same high temperature cvd	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:58
S18 4	0	restore same crystal structure same high temperature cvd	US-PGPUB; USPAT	ADJ	ON	2007/05/30 07:58
S18 5	2	restore same crystal structure same cvd	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:01
S18 6	3784	annealing same sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:01
S18 7	1925	annealing same sidewalls and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:01
S18 8	114	annealing same sidewalls same amorphous and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:03
S18 9	3	annealing near sidewalls same amorphous and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:04

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S19 0	0	cvd near sidewalls same amorphous and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:38
S19 1	2	chemical vapor deposition near sidewalls same amorphous and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:40
S19 2	7	heat same form near sidewalls same amorphous and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:06
S19 3	5	heat treatment same form near sidewalls same amorphous and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:08
S19 4	0	heat treatment same form near sidewalls same during same restore same crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:08
S19 5		heat treatment same form near sidewalls with crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:22
S19 6	Ó	heat treatment same form near sidewalls with recrystallize and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:22
S19 7	69	heat treatment same form near sidewalls and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:24
S19 8	0	low pressure cvd same form same sidewalls same restore near crystal structure and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:25
S19 9	0	low pressure cvd same form same sidewalls same crystal structure and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:25
S20 0	. 0	low pressure cvd same sidewalls same crystal structure and @py<"2004"	US-PGPUB; USPAT	ADJ	ON .	2007/05/30 08:25
S20 1	2	low pressure cvd same sidewalls same crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:41
S20 2	0	low pressure cvd near form near sidewalls same amorphous and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 08:39
\$20 3	0	low pressure cvd near form near sidewalls same crystal and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 08:39

S20 4	0	low pressure cvd same form near sidewalls same crystal and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 08:39
S20 5	2	low pressure cvd same form same sidewalls same crystal and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 08:39
S20 6	16	("4526593"   "4647494"   "5008207"   "5031029"   "5159508"   "5246884"   "5259918"   "5316958"   "5319240"   "5322813"   "5378922"   "5461243"   "5534079"   "5540785"   "5607511"   "5846867").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2007/05/30 08:39
\$20 7	2	chemical vapor deposition near sidewalls same amorphous and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 08:40
S20 8		low pressure cvd same sidewalls same crystal and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 08:41
'S20 9	0	low pressure cvd near frorming sidewalls same 550C and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 08:42
S21 0	0	low pressure cvd near forming sidewalls same 550C and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 08:42

S21 1	0	low pressure cvd near forming same sidewalls same 550C and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 08:42
S21 2	0	low pressure cvd same sidewalls same 550C and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 08:42
S21 3	170	low pressure cvd same sidewalls and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 08:43
S21 4	3488544	low pressure cvd and shibata-satoshi.in.	US-PGPUB; USPAT	OR	ON	2007/05/30 09:02
S21 5	1	low pressure cvd and shibata-satoshi.in.	US-PGPUB; USPAT	ADJ	ON	2007/05/30 09:03
S21 6	33	low pressure cvd and yu-bin.in.	US-PGPUB; USPAT	ADJ	ON	2007/05/30 09:05
S21 7	0	sidewalls same low pressure cvd and yu-bin.in.	US-PGPUB; USPAT	ADJ	ON	2007/05/30 09:04
S21 8	0	spacers same low pressure cvd and yu-bin.in.	US-PGPUB; USPAT	ADJ	ON	2007/05/30 09:04
S21 9	0	low pressure cvd same crystal and yu-bin.in.	US-PGPUB; USPAT	ADJ	ON	2007/05/30 09:06
S22 0	483	low pressure cvd same crystal	US-PGPUB; USPAT	ADJ	ON	2007/05/30 09:08
S22 1	5	low pressure cvd same crystal same (sidewalls or spacers)	US-PGPUB; USPAT	ADJ	ON	2007/05/30 09:07
S22 2	6	low pressure cvd same crystal same (sidewalls or spacers)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 09:07
S22 3	312	low pressure cvd same crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 09:09

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S22 4	2	sidewalls same formed same low pressure cvd same crystal and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 09:09
S22 5	3	sidewalls same formed same low pressure cvd same crystal and @py<"2004"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2007/05/30 09:09
S22 6	0	crystal same deep adj amorphous same (low pressure chemical vapor deposition or CVD) same form\$5 same sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/30 16:46
S22 7	0	crystal same deep adj amorphous same (low pressure chemical vapor deposition or CVD) same form same sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/30 16:46
S22 8	0	deep adj amorphous same (low pressure chemical vapor deposition or CVD) same form same sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/30 16:46
S22 9	0	deep adj amorphous same (low pressure chemical vapor deposition or CVD) same sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/30 16:46
S23 0	327	amorphous same (low pressure chemical vapor deposition or CVD) same sidewalls	US-PGPUB; USPAT	ADJ	ON	2007/05/30 16:47
S23 1	215	amorphous same (low pressure chemical vapor deposition or CVD) same sidewalls and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 16:47
S23 2	156	crystal same (low pressure chemical vapor deposition or CVD) same sidewalls and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 16:47
S23 3	156	crystal same (low pressure chemical vapor deposition or CVD) same sidewalls and @py<"2004"	US-PGPUB; USPAT	ADJ	ON	2007/05/30 16:48